



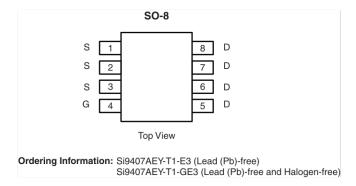
# P-Channel 60-V (D-S), 175 °C MOSFET

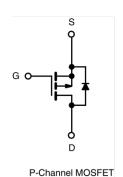
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)		
- 60	0.120 at V <sub>GS</sub> = - 10 V	± 3.5		
	0.15 at V <sub>GS</sub> = - 4.5 V	± 3.1		

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC







ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub> ± 20		¬	
Continuous Drain Current /T = 150 °C\8	T <sub>A</sub> = 25 °C	I <sub>D</sub>	± 3.5		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		± 3.0		
Pulsed Drain Current		I <sub>DM</sub>	± 30	A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.5		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	3.0	W	
	T <sub>A</sub> = 70 °C	] 'D	2.1		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	50	°C/W	

Notes:

a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$ 

## Si9407AEY

# Vishay Siliconix



<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Typ. <sup>a</sup>	Max.	Unit		
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zoro Goto Voltago Droin Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	μΑ		
Zero Gate Voltage Drain Current		$V_{DS}$ = - 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			- 10			
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 5 V, $V_{GS} =$ - 10 V	- 20			Α		
5	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = 3.5 A			0.120	Ω		
Drain-Source On-State Resistance <sup>D</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = 3.1 \text{ A}$			0.150			
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3.5 A		8		S		
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 2.5 A, V <sub>GS</sub> = 0 V			- 1.2	V		
Dynamic <sup>a</sup>								
Total Gate Charge	$Q_g$			18	30			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.5 \text{ A}$		5		nC		
Gate-Drain Charge	Q <sub>gd</sub>			2		1		
Turn-On Delay Time	t <sub>d(on)</sub>			8	15			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 30 $\Omega$		10	20			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$		35	50	ns		
Fall Time	t <sub>f</sub>			12	25			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.5 A, dI/dt = 100 A/μs		70	100			

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

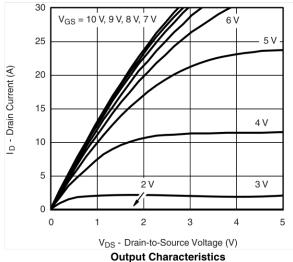
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

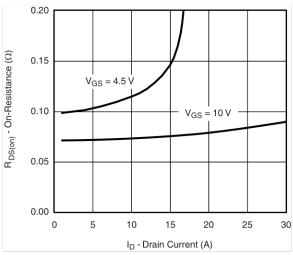




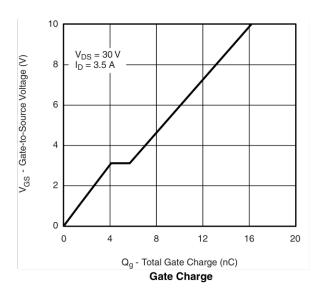
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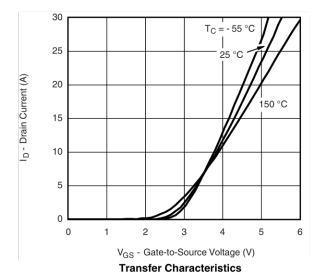


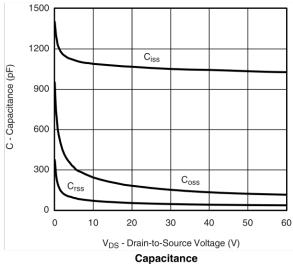


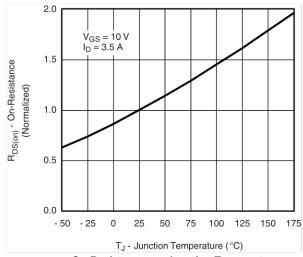


On-Resistance vs. Drain Current





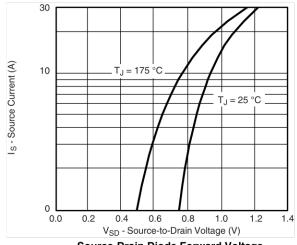




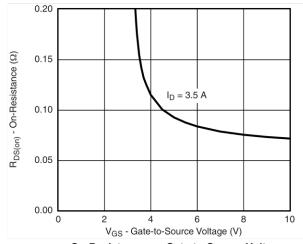
On-Resistance vs. Junction Temperature

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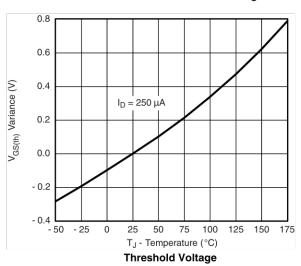
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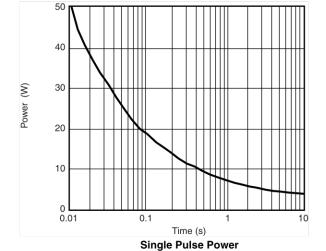


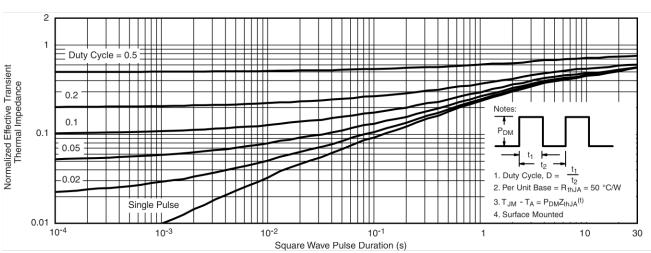
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage







Normalized Thermal Transient Impedance, Junction-to-Ambient

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